

Fig. 2 *In situ* variable temperature photoelectron spectra during the etching process starting from a freshly polished Ga-LLZO pellet (grey), heated to 800 °C under vacuum (orange-red), and cooled back down to room temperature (blue).

carbon could be important in determining the behaviour of the etched sample as a result of its increased electronic conductivity which might contribute to the observed low interfacial resistance with lithium metal. However, the uniformity of the coverage with carbonaceous species is unconfirmed in this case and so its effectiveness in promoting a homogeneous distribution of current is as yet unknown.

Alongside the removal of the carbonate species, the La 3d<sub>5/2</sub> core level also undergoes changes with the multiplet splitting increasing slightly from 4.4 eV to 4.6 eV, reaching a value more typical of La<sub>2</sub>O<sub>3</sub> (indicative of La in the LLZO lattice).<sup>14,21,25</sup> The lower initial value of 4.4 eV may correspond to the presence of some lanthanum oxycarbonate species,<sup>25</sup> which is removed by the etching process.

We finally note that the La 3p<sub>3/2</sub> and Ga 2p core level regions, which have the highest binding energies and thus lowest kinetic energies of the core levels measured, show a growth of the La and Ga signals at the surface as the carbonate/hydroxide layer is removed. This may seem surprising given the signals are normalised to the Zr 3d and thus might be expected to remain constant. However the low kinetic energies (~350 eV compared to ~1300 eV for Zr 3d) result in much shorter inelastic mean free paths for these photoelectrons and so the signal is much more surface sensitive and its intensity therefore varies with the thickness of carbonate/hydroxide layer.

### 3.3. ToF-SIMS depth profiling

As the XPS measurements have an information depth of up to 10 nm and average over a 300 × 700 μm spot size, we looked to the use of ToF-SIMS for depth profiling the samples to probe changes in cation species over a greater range of depths (several nanometers to several hundreds of nanometers).

SIMS analyses were performed using an Ar<sub>n</sub><sup>+</sup> (*n* ≈ 500) cluster sputter beam for gentle depth profiling of the samples, over an area spanning 200 × 200 μm. With this sputter beam, interaction of the ion beam with the sample is minimized, serving to preserve the nature of the surface under analysis better than other higher energy sputter beam species. For these set of experiments, vacuum transfer of the samples to the SIMS instrument was performed immediately following the surface treatment of each pellet, preventing the atmosphere of the glove box from interacting significantly with the surface. The ion counts are normalized to the sum of the total of all species under analysis here and plotted as a function of sputter ion fluence (proportional to sputter time and therefore depth). The <sup>6</sup>Li<sup>+</sup> minor isotope secondary ion species is chosen instead of <sup>7</sup>Li<sup>+</sup>, as the high yield of the latter leads to saturation of the SIMS detector which prevents all the <sup>7</sup>Li<sup>+</sup> secondary ion species being counted.

Fig. 3 shows the positive secondary ion profiles for two samples (etched and polished) using these conditions. The analysis area spans several grains, as seen in the ion maps in



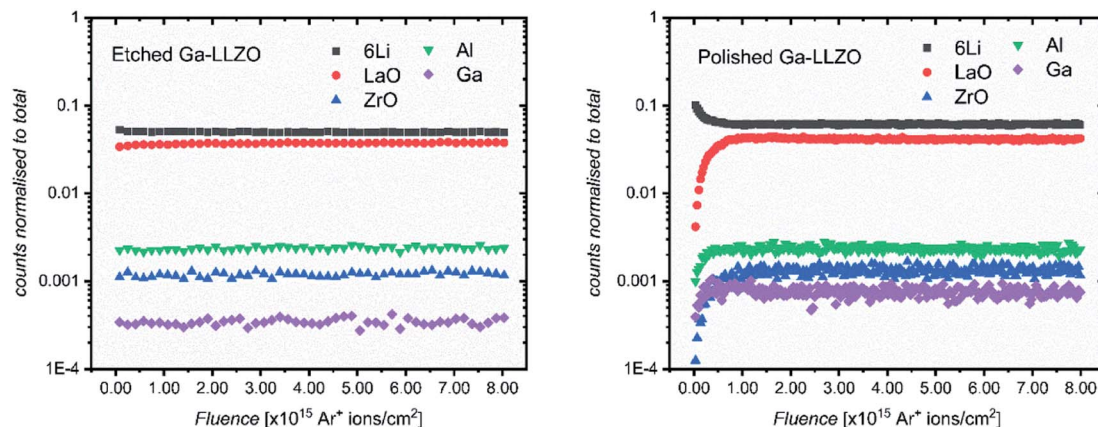


Fig. 3 ToF-SIMS depth profiles for etched and polished Ga-LLZO pellets, showing positive secondary ion species, operating under  $\text{Bi}^+$  primary beam (25 keV) and  $\text{Ar}_n^+$  (13.5 nA) sputter beam conditions.

Fig. S5.† In the etched case, the shape of the profiles for each species is relatively flat, indicating an unchanging surface chemistry with depth for the extent of the analysis, in addition to the avoidance of migration of species due to field-induced gradient effects caused by the sputter beam. This is in accordance with the notion that thermal etching cleans the surface of corrosion product impurities, as seen in the XPS results and in agreement with the literature.<sup>5,9,10</sup> On the other hand, the polished sample shows a region of changing ion counts at the near-surface, a region initially high in  $^6\text{Li}^+$  counts and poor in  $\text{LaO}^+$ ,  $\text{Ga}^+$ ,  $\text{Al}^+$  and  $\text{ZrO}^+$ , indicative of a Li-rich corrosion layer.

The etched samples show a slightly lower intensity of  $^6\text{Li}^+$  and higher intensity of  $\text{LaO}^+$  compared to the polished sample here. This is in accord with the *in situ* XPS data in which heating results in surface Li loss and changes to the nature of the surface La species.

The etched sample also has overall lower normalized counts for  $\text{Ga}^+$ . It is possible that the mobile gallium ions are thermally activated during the high temperature etching process, resulting either in gallium loss from the sample, or migration to

different lattice sites, leading to a change in the sample matrix and resulting change in yield of the  $\text{Ga}^+$  secondary ions during the SIMS process. We in fact observe a decrease in the concentration of Ga on the top side of the sintered pellets using Low Energy Ion Scattering (LEIS) depth profile analysis of the faces of Ga-LLZO (Fig. S6a†), proposed to be due to sublimation of Ga from the top surface during heating. Note that during etching, no mother powder is used to cover the pellets, which could promote more pronounced Ga (and Al) loss, despite the process occurring at a lower temperature and for a shorter time than the sintering process. It has also been described previously by Rettenwander<sup>26</sup> and Robben<sup>27</sup> that a symmetry reduction from the space group  $1a\bar{3}d$  to  $1\bar{4}3d$  can occur as a result of gallium substitution, which might be responsible for a variation in the Ga yield as seen in the SIMS analysis.

Next, in order to evaluate the activation of the surfaces after thermal etching, another set of SIMS measurements were made on similarly treated samples (polished and etched), but which were left in the glove box for several days prior to analysis. The same face of a single pellet was analyzed in each measurement

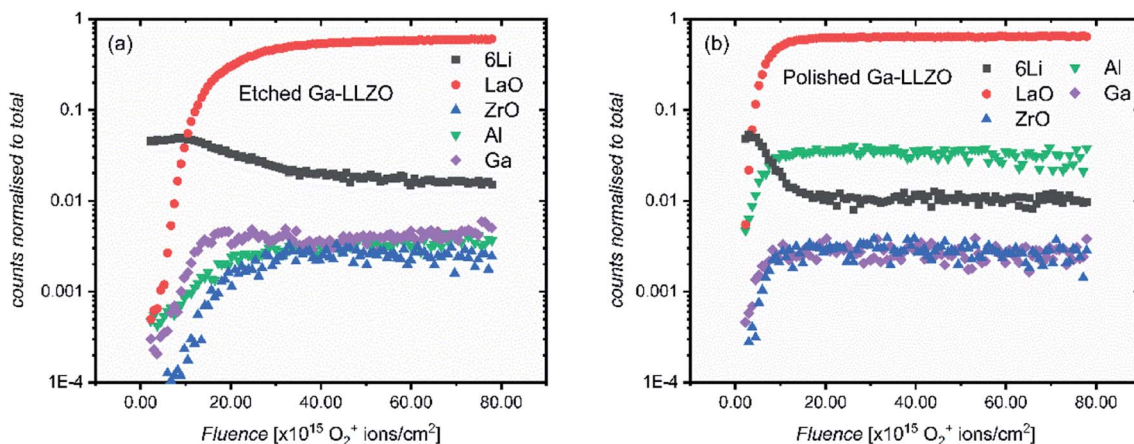


Fig. 4 ToF-SIMS depth profiles of etched (a) and polished (b) Ga-LLZO pellets, showing positive secondary ion species. The analysis was performed using 25 keV  $\text{Bi}^+$  primary ions as the analytical beam and the sputtering was performed by 1 keV 300 nA  $\text{O}_2^+$  beam (burst mode).



(the pellet was fractured and each resulting piece subject to a different surface treatment). As we expected to have a thick corrosion layer, an  $O_2^+$  sputter beam (1 kV, 300 nA) was selected. Traditionally, the  $O_2^+$  ion beam is thought to enhance the ionization probability for positive secondary ions by a surface chemical effect and provide stable ion yields. The higher current of the  $O_2^+$  beam meant that the sputtering of the materials proceeds more quickly than the argon cluster, meaning greater depths could be reached in shorter times.

Fig. 4 shows the depth profiles over an analysis area of 200 by 200  $\mu\text{m}$ , spanning several grains and grain boundaries (see Fig. 9 and S7† for ion images of the areas under analysis). This time, both etched and polished samples show an initial region of changing counts in their depth profiles – again with a surface region rich in  $Li^+$  and poor in  $LaO^+$ ,  $Ga^+$ ,  $Al^+$  and  $ZrO^+$  secondary ion yield, which here is more extended in the etched sample. We suggest that this region exists now even on the etched sample due to the presence of a corrosion layer following surface

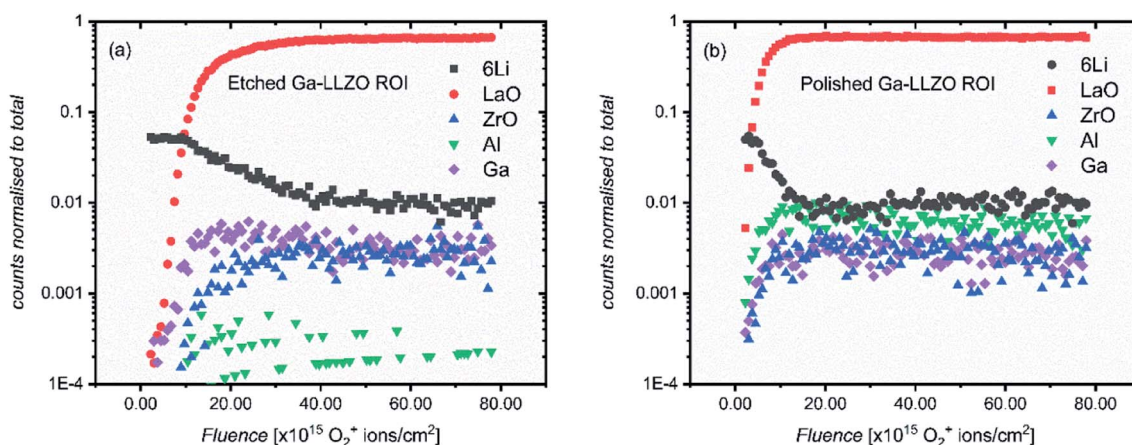


Fig. 5 ToF-SIMS depth profiles of etched (a) and polished (b) LLZO pellets, showing positive secondary ion species. Regions of interest (ROI) were selected based on areas without grain boundaries and pores in the etched and polished samples, respectively. The analysis was performed using 25 keV  $Bi^+$  primary ions as the analytical beam and the sputtering was performed by 1 keV 300 nA  $O_2^+$  beam (burst mode).

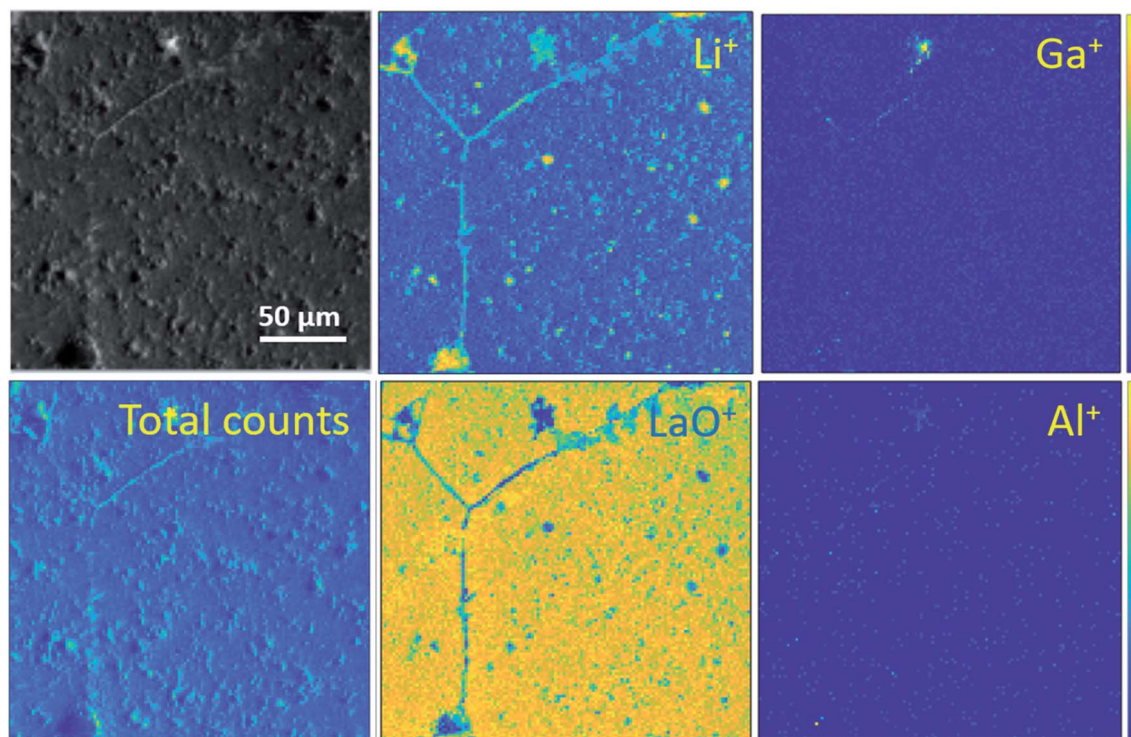


Fig. 6 ToF-SIMS positive secondary ion maps and optical image (greyscale) of etched sample, corresponding to the depth profiles of the etched samples in Fig. 4a and 5a. The analysis was performed using 25 keV  $Bi^+$  primary ions as the analytical beam and the sputtering was performed by 1 keV  $O_2^+$  beam (burst mode).



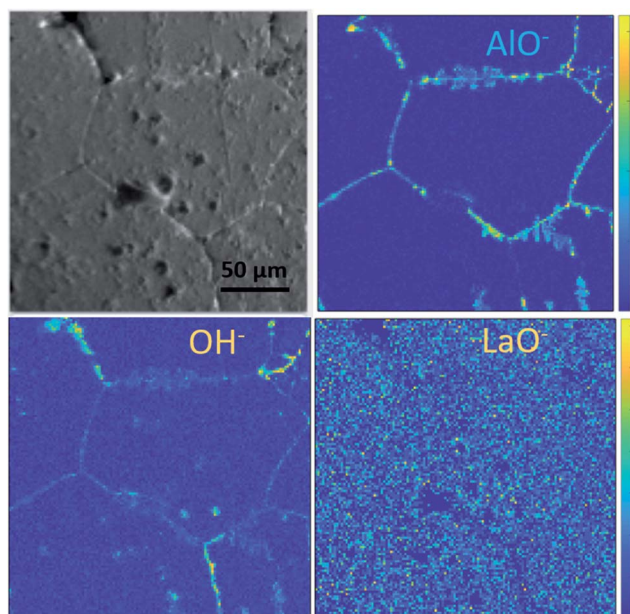


Fig. 7 ToF-SIMS negative secondary ion maps and optical image (greyscale) of an etched LLZO sample. The analysis was performed using 25 keV Bi<sup>+</sup> primary ions as the analytical beam and the sputtering was performed by 1 keV O<sub>2</sub><sup>+</sup> beam (burst mode).

reaction inside the glove box by direct reaction with residual CO<sub>2</sub> (also seen by Zhu *et al.*<sup>2</sup>). As the region is more extended in the etched sample, this could suggest that the etched sample surface is in some way more activated than the polished sample, making it more reactive and susceptible to facile physisorption of contaminants present in the glove box such as CO<sub>2</sub>. Changes to the surface morphology (as seen in the SEM images of polished and etched samples in Fig. S2†), as well as chemical modification effects at the surface, might be responsible for this behavior.

To verify the presence of a corrosion layer, and to rule out beam-sample interaction effects which might lead to preferential and delayed sputtering of species, carbon and hydrogen-containing species were also followed in the depth profiles. Fig. S8† shows depth profiles containing multiple secondary ion species which could originate from a corrosion layer, such as

LiH<sup>+</sup>, CH<sub>3</sub>O<sup>+</sup>, CH<sub>2</sub>OLi<sup>+</sup>, CHOLi<sup>+</sup>, H<sup>+</sup> and CH<sub>2</sub><sup>+</sup>. The profiles of these species correlate well with the profiles of <sup>6</sup>Li<sup>+</sup> in both etched and polished samples (and showing an anticorrelation with ZrO<sup>+</sup>, LaO<sup>+</sup>), agreeing with this hypothesis. In addition, *ex situ* room temperature XPS was performed on the samples. In agreement with the SIMS depth profiles, a thicker corrosion layer was found to have formed on the etched sample, with a higher at% of carbon-based species found on the etched sample (Table S1†). In order to assess the effect of this rapidly-formed corrosion layer on pellets left in the glove box after thermal etching, EIS was carried out on a cell assembled ~16 h after thermal etching (Fig. S9†), showing an increase in the interfacial resistance when compared with the impedance measured for a cell assembled immediately after thermal etching.

It can also be seen in Fig. 4 that the <sup>6</sup>Li<sup>+</sup> counts are eventually lower than the LaO<sup>+</sup> counts at the end of each profile. This is in contrast with the depth profiles in Fig. 3, in which the LaO<sup>+</sup> counts are always higher after the initial corrosion layer. We attribute this to two things. Firstly, to the more extensive formation of corrosion products during sample storage, which consumes more lithium from the bulk of the LLZO. Secondly, to the use of a different sputter gun which results in a change in the yield of secondary ion species. Given the high mobility of lithium in LLZO structure, these samples show a corresponding depletion of Li in the bulk of the samples probed by SIMS, indicating a slightly lithium-poor defective garnet.

It is also notable that in the polished sample, as well as having a thinner corrosion region, the relative intensities of the secondary ion species differ from those of the etched sample – Al<sup>+</sup> has a higher number of counts than the etched sample. By ensuring the same side of the same mother pellet was measured, changes in cation concentrations due to differences in the chemistry of different pellet faces can be ruled out here. To elaborate: during sintering the formation of an Al<sub>2</sub>O<sub>3</sub>–Li<sub>2</sub>O eutectic leads to an Al concentration gradient through the sample, coupled with Al loss from the top surface, with the concentration highest on the side of the pellet previously in contact with the alumina crucible during sintering. This is seen by LEIS depth profiles of both sides of a sintered Ga-LLZO pellet, in which the normalised Al content is higher on the bottom face of the pellet, as shown in Fig. S6b.†

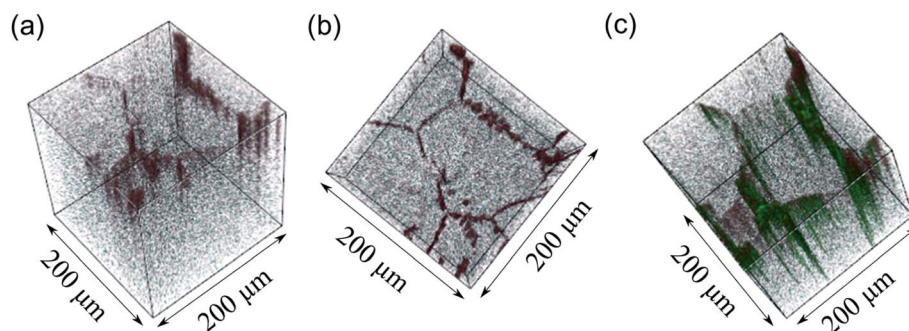


Fig. 8 Three-dimensional reconstruction with negative secondary ions of the etched Ga-LLZO sample. LaO<sup>−</sup> represents the bulk LLZO grains in dark green and OH<sup>−</sup> at the grain boundary surface in brown (a and b). The grain boundaries also contain AlO<sup>−</sup> in green (c).





and electronic conductivity as well as the chemical reactivity/stability of the grains and grain boundaries in these materials, with the possibility of tailoring the grain boundary composition to achieve a desired chemical stability and ionic transport behaviour.<sup>30</sup> In the etched sample, the counts for  $\text{Al}^+$  are too low (low yield of  $\text{Al}^+$  secondary ion species) to be able to compare its appearance within the grains and at grain boundaries in the image, so instead the negative ion species were followed (Fig. 7).

The polished sample, however, has a clear segregation of  $\text{Al}^+$  at pores (see Fig. S7†), which agrees with the depth profile results in which we saw a significant lowering of the  $\text{Al}^+$  counts when the pore regions were excluded from the analysis (Fig. 5). These Al-rich 'pockets' have been described by Doeff and co-workers,<sup>20</sup> and here may be more prominent in the SIMS maps as the Al might originate from a different Al-rich phase than that found in the grain boundaries or grains of the etched sample (resulting in different secondary ion yields).

Looking at the negative secondary ion maps of an etched sample (Fig. 7), the presence of Al in the grain boundaries (indicated by  $\text{AlO}^-$  secondary ions) is much clearer. It is likely that differences in intensities of detected Al secondary ions in the etched and polished samples originate from difference in the matrix from which they are created (the Al-containing species in the pores *versus* the grain boundaries likely differ in identity). The grain boundaries also appear rich in  $\text{OH}^-$ ,

suggesting a reaction to form corrosion products. In fact, three-dimensional reconstructed images show an accumulation of  $\text{OH}^-$  along the grain boundaries close to the surface only (Fig. 8). The significant reactivity of grain boundaries during proton–lithium exchange was previously reported, in which a significant increase in grain boundary resistance accompanying the exchange process in LLZO pellets was observed.<sup>11</sup> A schematic of the various proposed processes occurring following thermal and atmospheric treatment of the Ga-LLZO pellets as described in this work is given in Fig. 9.

It was previously noted that the relative intensities of some secondary ion species (especially  $\text{Ga}^+$  and  $\text{Al}^+$ ) collected in the SIMS depth profiles varied from measurement to measurement, even on different areas of the same sample. To investigate this, post-processing of depth profiles collected on a region of etched sample consisting of multiple grains was performed, and the resultant reconstructed depth profiles were compared. Two such regions are highlighted in Fig. 10 (for a complete comparison of all grains in the field of view, see Fig. S11†). Interestingly, a significant difference in the  $\text{Al}^+$  intensity can be seen across the two ROIs, with the relative intensity being much higher for  $\text{Al}^+$  in the smaller, central grain (ROI 1). This would indicate that the pellet microstructure influences the chemistry of grains and grain boundaries which could be the reason for the impact of grain size on electrochemical performance previously reported.<sup>20,31</sup>

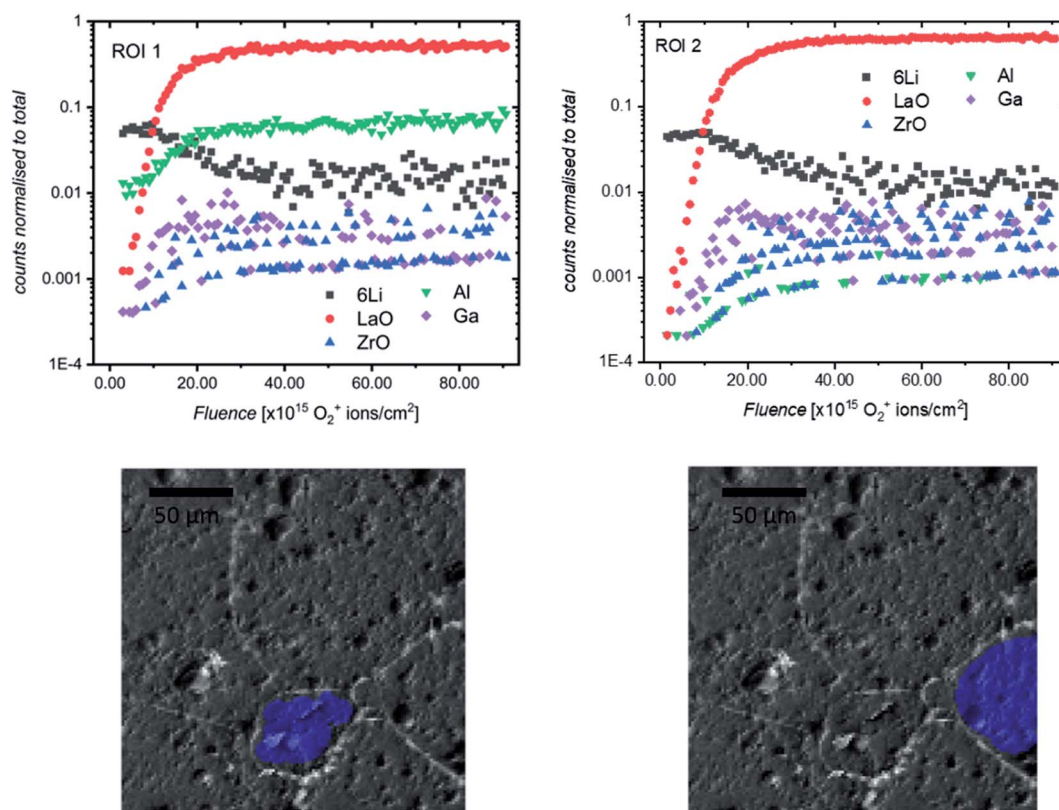


Fig. 10 ToF-SIMS positive secondary ion depth profiles and corresponding region of interest (ROI) highlighted on optical images (greyscale) of an etched LLZO sample. The analysis was performed using 25 keV  $\text{Bi}^+$  primary ions as the analytical beam and the sputtering was performed by 1 keV  $\text{O}_2^+$  beam (burst mode).





